

PTC-1449 REPRODUCED

ATTORNEY DOCKET NO.  
0717.2033-002APPLICATION NO.  
10/608,780INFORMATION DISCLOSURE CITATION  
IN AN APPLICATIONFIRST NAMED INVENTOR  
Jagdish NarayanFILING DATE  
June 27, 2003

March 24, 2004

EXAMINER  
Not yet assignedCONFIRMATION NO.  
8117GROUP  
2811

(Use several sheets if necessary)

## U.S. PATENT DOCUMENTS

EXAM- INER INI- TIAL	REF. NO.	DOCUMENT NUMBER Number-Kind Code (if known)	ISSUE DATE / PUBLICATION DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT
BT	AA	4,153,905	05-08-1979	Charmakadze <i>et al.</i>
	AB	4,495,514	01-22-1985	Lawrence <i>et al.</i>
	AC	4,670,088	06-02-1987	Tsaur <i>et al.</i>
	AD	4,946,548	08-07-1990	Kotaki <i>et al.</i>
	AE	4,966,862	10-30-1990	Edmond
	AF	5,091,333	02-25-1992	Fan <i>et al.</i>
	AG	5,210,051	05-11-1993	Carter, Jr.
	AH	5,239,188	08-24-1993	Takeuchi <i>et al.</i>
	AI	5,247,533	09-21-1993	Okazaki <i>et al.</i>
	AJ	5,272,108	12-21-1993	Kozawa
	AK	5,278,433	01-11-1994	Manabe <i>et al.</i>
	AA2	5,281,830	01-25-1994	Kotaki <i>et al.</i>
	AB2	5,285,078	02-08-1994	Mimura <i>et al.</i>
	AC2	5,290,393	03-01-1994	Nakamura
	AD2	5,306,662	04-26-1994	Nakamura <i>et al.</i>
	AE2	5,323,022	06-21-1994	Glass <i>et al.</i>
	AF2	5,334,277	08-02-1994	Nakamura
	AG2	5,369,289	11-29-1994	Tamaki <i>et al.</i>
	AH2	5,385,862	01-31-1995	Moustakas
	AI2	5,406,123	04-11-1995	Narayan
	AJ2	5,408,120	04-18-1995	Manabe, <i>et al.</i>
	AK2	5,433,169	07-18-1995	Nakamura
	AA3	5,468,678	11-21-1995	Nakamura <i>et al.</i>
	AB3	5,578,839	11-26-1996	Nakamura, <i>et al.</i>
	AC3	5,563,422	10-08-1996	Nakamura, <i>et al.</i>
DN	AD3	5,652,434	07-29-1997	Nakamura, <i>et al.</i>

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PN	AE3	5,686,738	11-11-1997	Moustakas
	AF3	5,733,796	03-31-1998	Manabe <i>et al.</i>
	AG3	5,734,182	03-31-1998	Nakamura <i>et al.</i>
	AH3	5,747,832	05-05-1998	Nakamura <i>et al.</i>
	AI3	5,751,752	05-12-1998	Shakuda
	AJ3	5,767,581	06-16-1998	Nakamura <i>et al.</i>
	AK3	5,777,350	07-07-1998	Nakamura <i>et al.</i>
	AA5	5,828,684	10-27-1998	Van de Walle
	AB4	5,850,410	12-15-1998	Kuramata
	AC4	5,877,558	03-02-1999	Nakamura <i>et al.</i>
	AD4	5,880,486	03-09-1999	Nakamura <i>et al.</i>
	AE4	5,905,276	05-18-1999	Manabe <i>et al.</i>
	AF4	5,959,307	09-28-1999	Nakamura <i>et al.</i>
	AG4	5,998,925	12-07-1999	Shimizu <i>et al.</i>
	AH4	6,017,774	01-25-2000	Yuasa, <i>et al.</i>
	AI4	6,051,849	04-18-2000	Davis <i>et al.</i>
	AJ4	6,066,861	05-23-2000	Höhn <i>et al.</i>
	AK4	6,069,440	05-30-2000	Shimizu <i>et al.</i>
	AA5	6,078,063	06-20-2000	Nakamura <i>et al.</i>
	AB5	6,084,899	07-04-2000	Shakuda
	AC5	6,093,965	07-25-2000	Nakamura <i>et al.</i>
	AD5	6,115,399	09-05-2000	Shakuda
	AE5	6,153,010	11-28-2000	Kiyoku <i>et al.</i>
	AF5	6,172,382 B1	01-09-2001	Nagahama <i>et al.</i>
	AG5	6,204,512 B1	03-20-2001	Nakamura <i>et al.</i>
PN	AH5	6,215,133 B1	04-10-2001	Nakamura <i>et al.</i>

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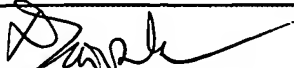
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PN	AI6	6,245,259 B1	06-12-2001	Höhn <i>et al.</i>
	AJ5	6,249,012 B1	06-19-2001	Manabe <i>et al.</i>
	AK5	6,337,493 B1	01-08-2002	Tanizawa <i>et al.</i>
	AA6	6,362,017 B1	03-26-2002	Manabe <i>et al.</i>
	AB6	US 2001/0022367 A1	09-20-2001	Nakamura <i>et al.</i>
	AC6	US 2001/0030318 A1	10-18-2001	Nakamura <i>et al.</i>
	AD6	US 2002/0046693 A1	04-25-2002	Kiyoku <i>et al.</i>
	AE6	US 2002/0060326 A1	05-23-2002	Manabe <i>et al.</i>
	AE6	US 2003/0199171 A1	10-23-2003	Rice <i>et al.</i>
	AG6	US 2003/0160246 A1	08-28-2003	Narayan <i>et al.</i>
	AH6	US 2001/0028062 A1	10-11-2001	Uemura <i>et al.</i>
	AI6	US 2003/0222263 A1	12-04-2003	Choi
	AJ6	US 2004/0000672 A1	01-01-2004	Fan <i>et al.</i>
	AK6	US 2004/0000671 A1	01-01-2004	Oh <i>et al.</i>
	AA7	US 2004/0000670 A1	01-01-2004	Oh <i>et al.</i>
	AB7	US 2001/0050375 A1	12-13-2001	Van Dalen
	AC7	5,383,088	01-17-1995	Chapple-Sokol <i>et al.</i>
	AD7	6,287,947 B1	09-11-2001	Ludowise <i>et al.</i>
	AE7	6,475,854 B2	11-05-2002	Narwankar <i>et al.</i>
	AF7	6,255,129 B1	07-03-2001	Lin
	AG7	6,097,040	01-01-2004	Morimoto <i>et al.</i>
	AH7	6,067,222	05-23-2000	Hausmann
	AI7	4,625,182	11-25-1986	Bovino <i>et al.</i>
	AJ7	6,241,344 B1	06-05-2001	Machida
	AK7	5,516,731	05-14-1996	Toutouchi <i>et al.</i>
PN	AA8	5,834,326	11-10-1998	Miyachi <i>et al.</i>

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FOREIGN PATENT DOCUMENTS						
		DOCUMENT NUMBER Country Code-Number-Kind Code (if known)	DATE MM-DD-YYYY	NAME OF PATENTEE OR APPLICANT OF CITED DOCUMENT	TRANSLATION YES	NO
PL	AL	JP9167857 (abstract only)	06-24-1997	Toshiba Corp		
	AM	JP 52/028887	03-04-1977	Fujitsu LTD		X
	AN	JP 05-243614	09-21-1993	Sharp Corp		X
	AO	JP 4236478	08-25-1992	Pioneer Electron Corp		X
	AP	JP 03-218625	09-26-1991	Univ Nagoya		X
	AQ	JP 03-252177 (abstract only)	11-11-1991	Toyoda Gosei Co LTD Toyoda Central Res & Dev Lab Univ Nagoya Res Dev Corp of Japan		
	AL2	JP 54-093380	07-24-1979	Fujitsu LTD		X
	AM2	JP 9092880 (abstract only)	04-04-1997	Toyoda Gosei Co LTD		
	AN2	JP 8213692	08-20-1996	Hitachi LTD		X
	AO2	JP 11145513 (abstract only)	05-28-1999	Sharp Corp		
	AP2	JP 04-068579	03-04-1992	Sharp Corp		X
	AQ2	JP 02-229475	09-12-1990	Nippon Telegr & Teleph Corp		X
	AL3	JP 04-242985 (abstract only)	08-31-1992	Toyoda Gosei Co LTD Akasaki Isamu Amano Hiroshi		
	AM3	JP9134881 (abstract only)	05-20-1997	Matsushita Electron Corp		
	AN3	JP 59-228776	12-22-1984	Nippon Telegr & Teleph Corp		X
	AO3	JP 06-177423	06-24-1994	Nichia Chem Ind LTD		X
	AP3	JP 06-268259	09-22-1994	Nichia Chem Ind LTD		X
	AQ3	JP 02-229475	09-12-1990	Nippon Telegr & Teleph Corp		X
	AL4	JP 2229475	09-12-1990	Nippon Telegr & Teleph Corp		X
	AM4	JP 06-021511	01-28-1994	Nippon Telegr & Teleph Corp		X
	AN4	JP 4209577	07-30-1992	Nippon Telegr & Teleph Corp		X
	AO4	JP 61-056474	03-22-1986	Matsushita Electric Ind Co LTD		X
PL	AP4	JP 8167735	06-25-1996	Hitachi Cable LTD		X

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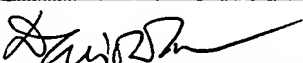
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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
Dr	AR	Foresi, J.S. and Moustakas, T.D., "Metal contacts to gallium nitride," <i>Appl. Phys. Lett.</i> 62(22):2859-2861 (1993).
	AS	Nakamura, S., "InGaN blue - light - emitting diodes," <i>Journal of the Institute of Electronics, Information and Communication Engineers</i> 76(9):913-917 (1993) (Abstract).
	AT	Akasaki, I. and Amano, H., "High efficiency UV and blue emitting devices prepared by MOVPE and low energy electron beam irradiation treatment," <i>Physical Concepts of Materials for Novel Optoelectronic Device Applications</i> , 1361:138-149 (1990).
	AU	Amano, H., <i>et al.</i> , "P-Type Conduction in Mg-Doped GaN Treated with Low-Energy Electron Beam Irradiation (LEEPI)," <i>Japanese Journal of Applied Physics</i> 28(12):L2112-L2114 (1989).
	AV	Andreev, V.M., <i>et al.</i> , "Luminescence Properties of i-n, i-n-i and n-i-n Structures Made of Epitaxial Layers GaN/ $\alpha$ -Al <sub>2</sub> O <sub>3</sub> ," <i>Journal of Luminescence</i> 35:9-16 (1986).
	AW	Boulou, M., <i>et al.</i> , "Recombination Mechanisms in GaN:Zn," <i>Journal of Luminescence</i> 18/19:767-770 (1979).
	AX	Casey, Jr., H.C. and Panish, M.B., "SLAB-Dielectric Waveguides," in <i>Heterostructure Lasers</i> , (NY: Academic Press), pp. 32-35 (1978).
	AY	Goldenberg, B., <i>et al.</i> , "Ultraviolet and violet light-emitting GaN diodes grown by low-pressure metalorganic chemical vapor deposition," <i>Appl. Phys. Lett.</i> 62(4):381-383 (1993).
	AZ	F. Goodenough, "Exotic Semiconductors Showcased at the IEDM," <i>Electronic Design</i> , pp. 60, 62, 64-66, 68 (1994).
	AY	Hayashi, I., <i>et al.</i> , "Junction Lasers Which Operate Continuously at Room Temperature," <i>Appl. Phys. Lett.</i> 17(3):109-111 (1970).
	AS2	Jacob, G., <i>et al.</i> , "GaN Electroluminescent Devices: Preparation and Studies," <i>Journal of Luminescence</i> 17:263-282 (1978).
	AT2	Jang, J.-S., <i>et al.</i> , "High Quality Non-Alloyed Pt Ohmic Contacts to P-Type GaN Using Two-Step Surface Treatment," <i>MRS Internet J. Nitride Semiconductor Res.</i> F99W10.4.
Dr	AU2	Kaminska, E., <i>et al.</i> , "Ni/Si-Based Contacts to GaN: Thermally Activated Structural Transformations Leading to Ohmic Behavior," <i>MRS Internet J. Nitride Semicond. Res.</i> 4S1, G9.9.



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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
AV2	Kampen, T.U. and Mönch, W., "Metal Contacts on a-GaN," <i>MRS Internet J. Nitride Semicond. Res.</i> 1(41).	
AW2	Madar, R., "High Pressure Solution Growth of GaN*," <i>Journal of Crystal Growth</i> 31:197-203 (1975).	
AX2	Matsuoka, T., "Growth and Properties of a Wide-Gap Semiconductor InGa <sub>N</sub> ," <i>Optoelectronics</i> 5(1):53-64 (1990).	
AY2	T. Matsuoka, "Current status of GaN and related compounds as wide-gap semiconductors," <i>Journal of Crystal Growth</i> 124:433-438 (1992).	
AZ2	Nakamura, S., <i>et al.</i> , "High-power InGa <sub>N</sub> /Ga <sub>N</sub> double-heterostructure violet light emitting diodes," <i>Appl. Phys. Lett.</i> 62(19):2390-2392 (1993).	
AR3	Nakamura, S., <i>et al.</i> , "P-GaN/N-InGa <sub>N</sub> /N-GaN Double-Heterostructure Blue-Light-Emitting Diodes," <i>Jpn. J. Appl. Phys.</i> 32:L8-L11 (1993).	
AS3	S. Nakamura, "Growth of In <sub>x</sub> Ga <sub>(1-x)</sub> N compound semiconductors and high-power InGa <sub>N</sub> /AlGa <sub>N</sub> double heterostructure violet-light-emitting diodes," <i>Microelectronics Journal</i> 25:651-659 (1994).	
AT3	Nakamura, S., <i>et al.</i> , "High-Power GaN P-N Junction Blue-Light-Emitting Diodes," <i>Japanese Journal of Applied Physics</i> 30(12A):L1998-L2001 (1991).	
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AV3	Nakamura, S., <i>et al.</i> , "Thermal Annealing Effects on P-Type Mg-Doped GaN Films," <i>Jpn. J. Appl. Phys.</i> 31:L139-L142 (1992).	
AW3	Nakamura, S., "Zn-doped InGa <sub>N</sub> growth and InGa <sub>N</sub> /AlGa <sub>N</sub> double-heterostructure blue-light-emitting diodes," <i>Journal of Crystal Growth</i> 145:911-917 (1994).	
AX3	Nakamura, S., <i>et al.</i> , "High-brightness InGa <sub>N</sub> /AlGa <sub>N</sub> double-heterostructure blue-green-light-emitting diodes," <i>J. Appl. Phys.</i> 76(12):8189-8191 (1994).	
AY3	Nakamura, S., <i>et al.</i> , "Cd-Doped InGa <sub>N</sub> Films Grown on GaN Films," <i>Jpn. J. Appl. Phys.</i> 32:L338-L341 (1993).	











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	AZ3	Nakamura, S., "High-Power InGaN/AlGaN Double-Heterostructure Blue-Light-Emitting Diodes," Int'l Electronic Devices Meeting 94:567-570 (1994).
	AR4	Piotrowska, A., et al., "Ohmic Contacts to III-V Compound Semiconductors: A Review of Fabrication Techniques," <i>Solid-State Electronics</i> 26(3):179-197 (1983).
	AS4	Sporken, R., et al., "XPS study of Au/GaN and Pt/GaN contacts," <i>MRS Internet J. Nitride Semiconductor Res.</i> 2(23)(1997).
	AT4	Venugopalan, H.S., et al., "Phase Formation and Morphology in Nickel and Nickel/Gold Contacts To Gallium Nitride," <i>MRS Internet Journal Nitride Semiconductor Research</i> (1997) <URL:http://nsr.mij.mrs.org/MRS/S97-D/4.10>.
	AU4	Zhou, L., et al., "Characteristics of Ti/Pt/Au Ohmic Contacts on p-type GaN/Al <sub>x</sub> Ga <sub>1-x</sub> N Superlattices," <i>MRS Internet J. Nitride Semicond. Res.</i> F99W10.3.
	AY4	Dovidenko, K., et al., "Aluminum nitride films on different orientations of sapphire and silicon," <i>J. Appl. Phys.</i> 79(5): 2439-2445, (1996).
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	AX4	Lin, Y.S., et al., "Dependence of composition fluctuation on indium content in InGa <sub>x</sub> N/GaN multiple quantum wells," <i>Appl. Phys. Lett.</i> , 77(19): 2988-2990, (2000).
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	AZ4	Kawakami, Y., et al., "Dynamics of optical gain in In <sub>x</sub> Ga <sub>1-x</sub> N multi- quantum well-based laser diodes," <i>Appl. Phys. Lett.</i> , 77(14): 2151-2153, (2000).
	AR5	Strite, S., and Morkoc, H., "GaN, AlN, and InN: A review," <i>J. Vac. Sci. Technol. B</i> , 10(4):1237-1266, (1992).
	AS5	Hassan, K.M., et al., "Optical and structural studies of Ge nanocrystals embedded in AlN matrix fabricated by pulsed laser deposition," <i>Appl. Phys. Lett.</i> , 75(9): 1222-1224, (1999).
	AT5	Teng, C.W., et al., "Quantum confinement of E <sub>1</sub> and E <sub>2</sub> transitions in Ge quantum dots embedded in an Al <sub>2</sub> O <sub>3</sub> or an AlN matrix," <i>App. Phys. Lett.</i> , 76(1): 43-45, (2000).

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OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
	AU5	Narukawa, Y., <i>et al.</i> , "Role of self-formed InGaN quantum dots for exciton localization in the purple laser diode emitting at 420 nm," <i>Appl. Phys. Lett.</i> , 70(8): 981-983, (1997).
	AV5	Nakamura, S., "The Roles of Structural Imperfections in InGaN-Based Blue Light-Emitting Diodes and Laser Diodes," <i>Science Magazine</i> , 1-14, [retrieved online 2000-08-08]. Retrieved from the Internet <URL: <a href="http://www.science.org/cgi/content/full/281/5379/956">http://www.science.org/cgi/content/full/281/5379/956</a> >.
	AW5	Chichibu, S., <i>et al.</i> , "Spatially resolved cathodoluminescence spectra of InGaN-quantum wells," <i>App. Phys. Lett.</i> , 71(16): 2346-2348, (1997).
	AX5	Queisser, H.J., <i>et al.</i> , "Defects in Semiconductors: Some Fatal, Some Vital," <i>Science</i> , 281:945-950 (1998).
	AY5	LeGoues, F. K., <i>et al.</i> , "Cyclic Growth of Strain-Relaxed Islands," <i>Physical Review Letters</i> , 73(2):300-303 (1994).
	AZ5	Mahajan, S., "Defects in Semiconductors and Their Effects on Devices," <i>Acta Materialia</i> , 48:137-149 (2000).
	AR6	Matthews, J.W., <i>et al.</i> , "Defects in Epitaxial Multilayers," <i>Journal of Crystal Growth</i> , 27:118-125 (1974).
	AS6	Narayan, J., <i>et al.</i> , "Mechanism of Formation of 60° and 90° Misfit Dislocations in Semiconductor Heterostructures," <i>Materials Science and Engineering</i> , B10:261-267 (1991).
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EXAMINER 	DATE CONSIDERED 3/23/05
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